

REMARKS

New claim 27 tracks previously allowed claim 6 from this application's parent application – except that this new claim substitutes hydrogen peroxide for tetramethyl ammonium hydroxide and adds the step of applying sonic energy while the high-k gate dielectric layer is exposed to the solution that comprises hydrogen peroxide. Support for elements added to new claim 27, and new dependent claims 28-31, appears in the specification at page 7, lines 1-7, which provides:

When high-k gate dielectric layer 110 is exposed to a hydrogen peroxide based solution, an aqueous solution that contains between about 2% and about 30% hydrogen peroxide by volume may be used. That exposure step should take place at between about 15°C and about 40°C for at least about one minute. In a particularly preferred embodiment, high-k gate dielectric layer 110 is exposed to an aqueous solution that contains about 6.7% H₂O₂ by volume for about 10 minutes at a temperature of about 25°C.

and at page 8, lines 8-13, which provides:

While high-k gate dielectric layer 110 is exposed to a solution that comprises a source of hydroxide, it may be desirable to apply sonic energy at a frequency of between about 10 KHz and about 2,000 KHz, while dissipating at between about 1 and about 10 watts/cm². In a preferred embodiment, sonic energy may be applied at a frequency of about 1,000 KHz, while dissipating at about 5 watts/cm².

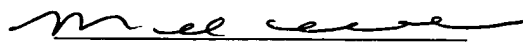
Applicants respectfully request the examiner to allow new pending claims
27-31 to issue.

If there are any additional charges, please charge Deposit Account No.
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Respectfully submitted,

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